

MOSFET - Power, Single P-Channel, WDFN8 -100 V, 120 mΩ, -13 A



ON Semiconductor®

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NTTFS115P10M5

Features

- Small Footprint (3.3 x 3.3 mm) for Compact Design
- These Devices are non-ESD Protected
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	-100	V
Gate-to-Source Voltage	V _{GS}	±20	V
Continuous Drain Current R _{θJC} (Note 2)	I _D	T _C = 25°C	-13
		T _C = 100°C	-8.0
Power Dissipation R _{θJC} (Note 2)	P _D	T _C = 25°C	41
		T _C = 100°C	16
Continuous Drain Current R _{θJA} (Notes 1, 2)	I _D	T _A = 25°C	-2.0
		T _A = 100°C	-1.1
Power Dissipation R _{θJA} (Notes 1, 2)	P _D	T _A = 25°C	0.9
		T _A = 100°C	0.3
Pulsed Drain Current	T _A = 25°C, t _p = 10 μs	I _{DM}	-137
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
Source Current (Body Diode)	I _S	-34	A
Single Pulse Drain-to-Source Avalanche Energy (I _{L(pk)} = -9.1 A)	E _{AS}	41	mJ
Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)	T _L	260	°C

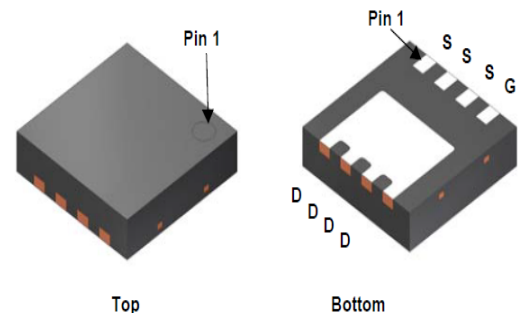
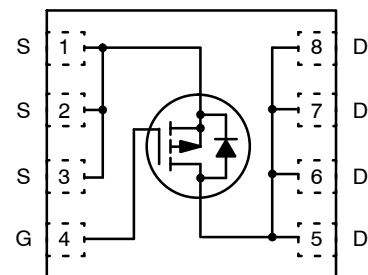
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case - Steady State (Note 2)	R _{θJC}	3.0	°C/W
Junction-to-Ambient - Steady State (Note 2)	R _{θJA}	134	

1. Surface-mounted on FR4 board using a 1 in² pad size, 1 oz Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

V _{(BR)DSS}	R _{DS(on)} MAX	I _D MAX
-100 V	120 mΩ @ -10 V	-13 A
	254 mΩ @ -6 V	



WDFN8
CASE 511DH

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	-100			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\ \mu\text{A}$, ref to 25°C		-67		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = -80\text{ V}$	$T_J = 25^\circ\text{C}$		-1	μA
			$T_J = 125^\circ\text{C}$		-100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -45\ \mu\text{A}$	-2.0	-3.0	-4.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = 250\ \mu\text{A}$, ref to 25°C		6.2		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -2.4\text{ A}$		97	120	$\text{m}\Omega$
		$V_{GS} = -6\text{ V}, I_D = -1.6\text{ A}$		127	254	
Forward Transconductance	g_{FS}	$V_{DS} = -10\text{ V}, I_D = -2.1\text{ A}$		5.5		S
Gate-Resistance	R_G	$T_A = 25^\circ\text{C}$		3.5		Ω

CHARGES & CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = -50\text{ V}$		637		pF
Output Capacitance	C_{OSS}			93.5		
Reverse Transfer Capacitance	C_{RSS}			4.5		
Total Gate Charge	$Q_G(\text{TOT})$	$V_{GS} = -6\text{ V}, V_{DS} = -50\text{ V}, I_D = -2.4\text{ A}$		5.7		nC
Total Gate Charge	$Q_G(\text{TOT})$	$V_{GS} = -10\text{ V}, V_{DS} = -50\text{ V}, I_D = -2.4\text{ A}$		9.2		
Gate-to-Source Charge	Q_{GS}			3.0		
Gate-to-Drain Charge	Q_{GD}			1.3		
Plateau Voltage	V_{GP}			4.4		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -10\text{ V}, V_{DS} = -50\text{ V}, I_D = -2.4\text{ A}, R_G = 2.5\ \Omega$		8.7		ns
Rise Time	t_r			2.1		
Turn-Off Delay Time	$t_{d(OFF)}$			13.4		
Fall Time	t_f			4.1		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = -2.4\text{ A}$	$T_J = 25^\circ\text{C}$		0.84	1.2	V
			$T_J = 125^\circ\text{C}$		0.71		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, \text{d}I_S/\text{d}t = 300\text{ A}/\mu\text{s}, I_S = -1.2\text{ A}$		28.7		ns	
Reverse Recovery Charge	Q_{RR}			87.6		nC	
Charge Time	t_a			18.4		ns	
Discharge Charge	t_b			10.4		ns	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures.

4. Pulse Test: Pulse Width < 300 μs . Duty Cycle < 2%.

5. Maximum current for pulses as long as 1s is higher but is independent on pulse duration or duty cycles.

TYPICAL CHARACTERISTICS

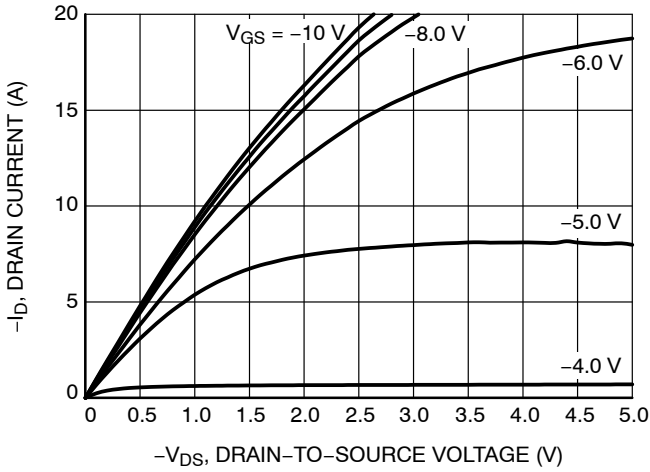


Figure 1. On-Region Characteristics

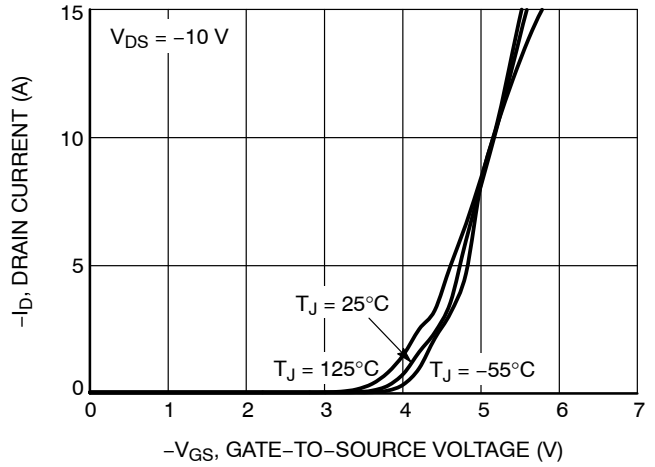


Figure 2. Transfer Characteristics

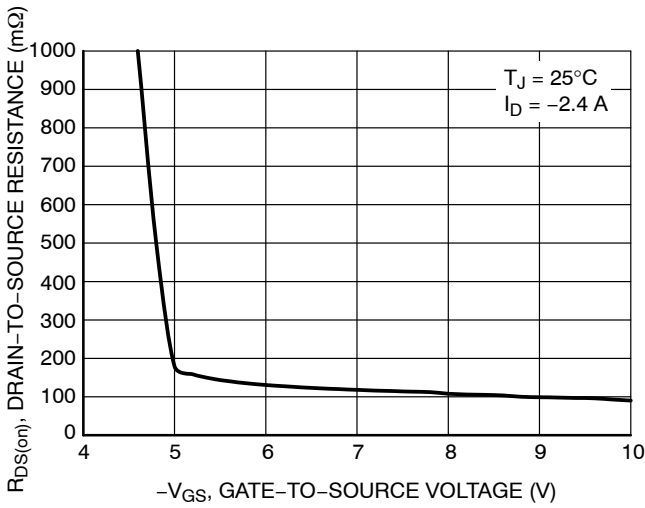


Figure 3. On-Resistance vs. Gate-to-Source Voltage

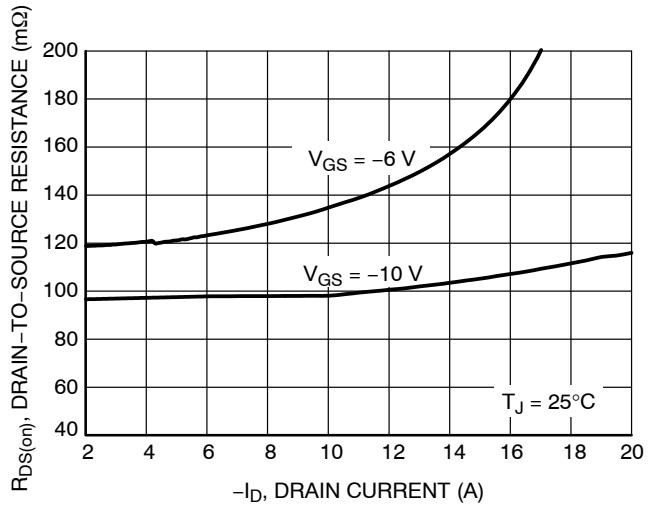


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

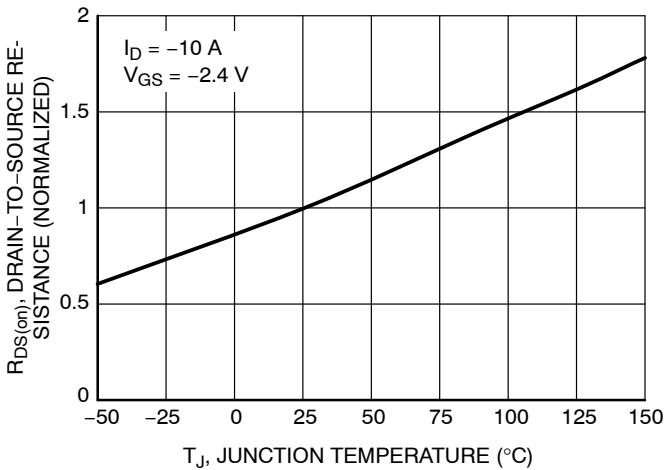


Figure 5. On-Resistance Variation with Temperature

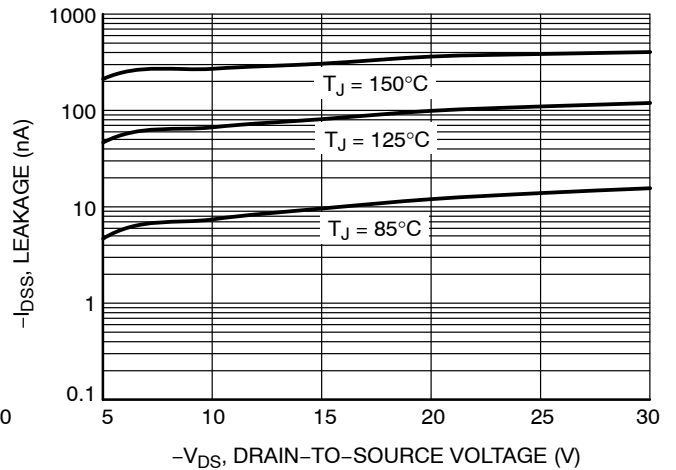


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

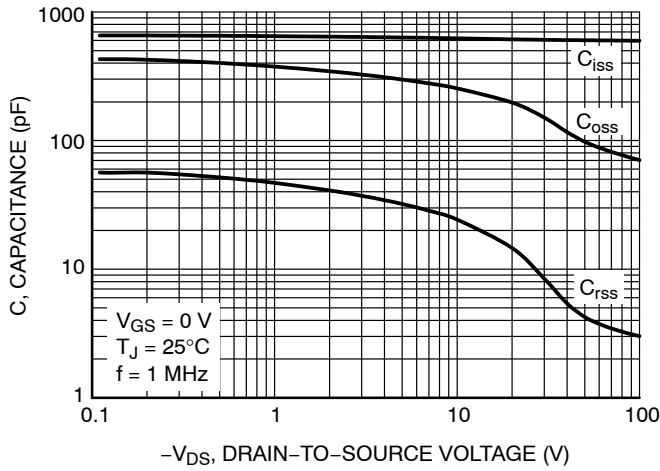


Figure 7. Capacitance Variation

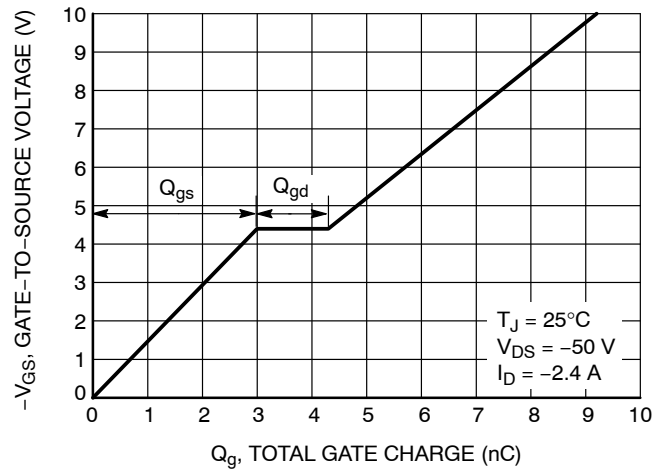


Figure 8. Gate-to-Source vs. Total Charge

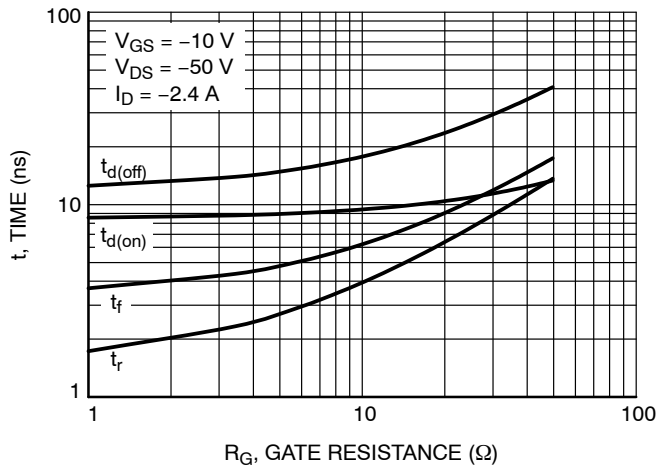


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

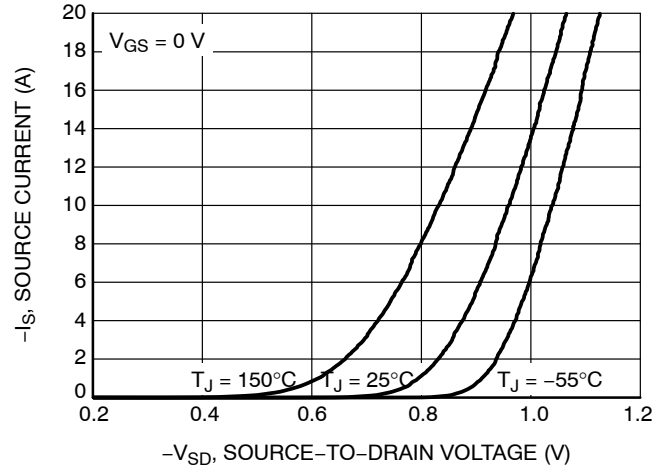


Figure 10. Diode Forward Voltage vs. Current

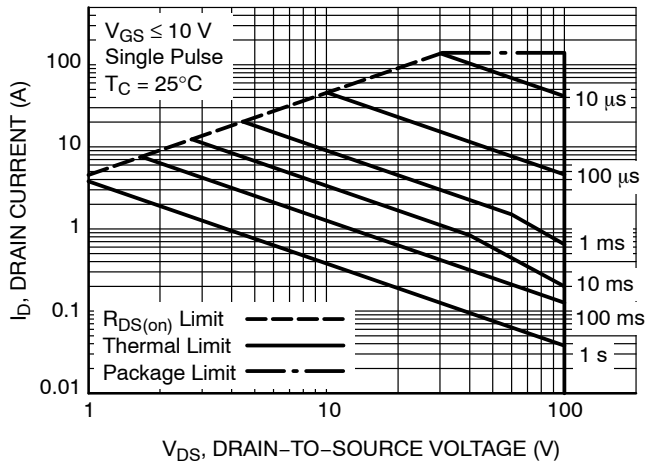


Figure 11. Maximum Rated Forward Biased Safe Operating Area

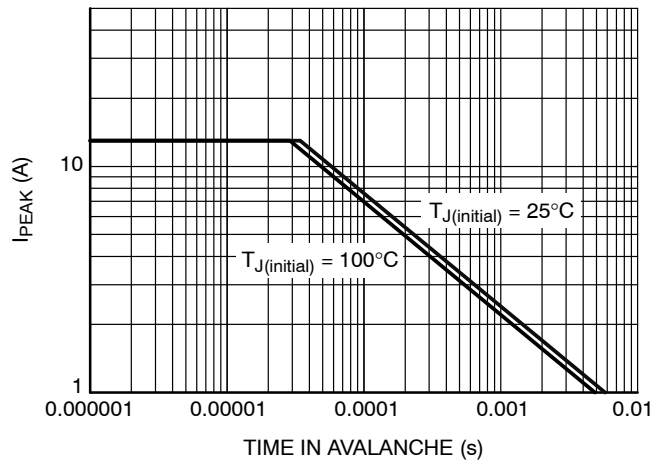


Figure 12. I_{PEAK} vs. Time in Avalanche

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TYPICAL CHARACTERISTICS

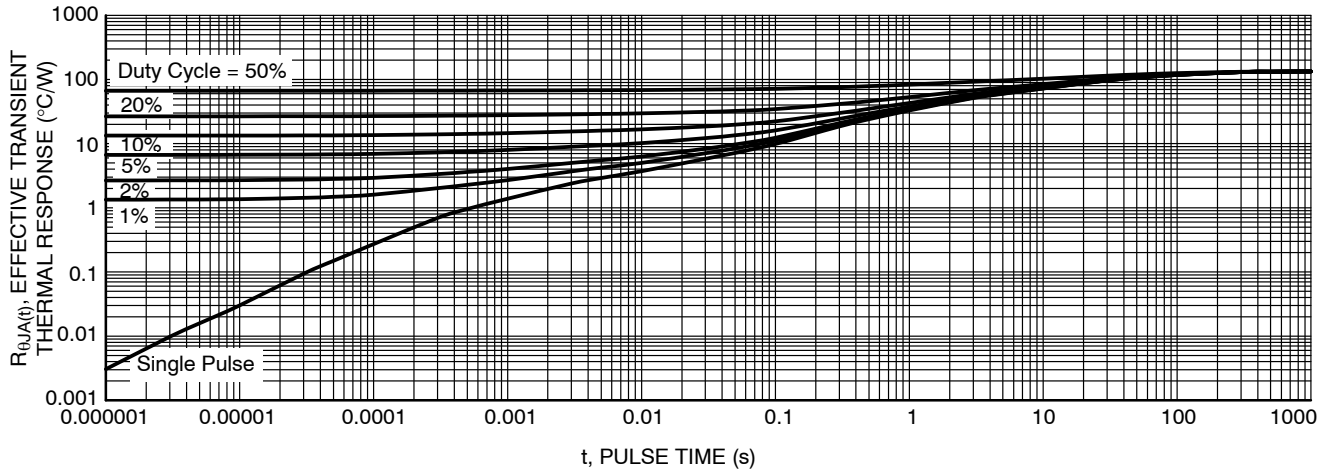


Figure 13. Thermal Response

DEVICE ORDERING AND MARKING INFORMATION

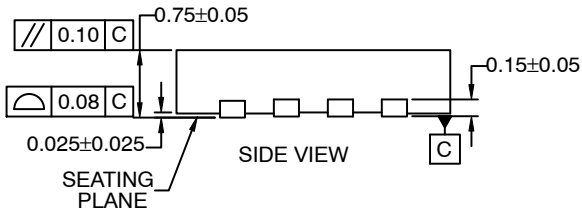
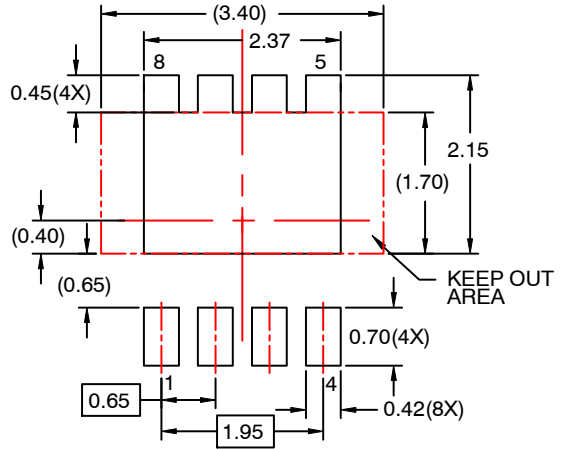
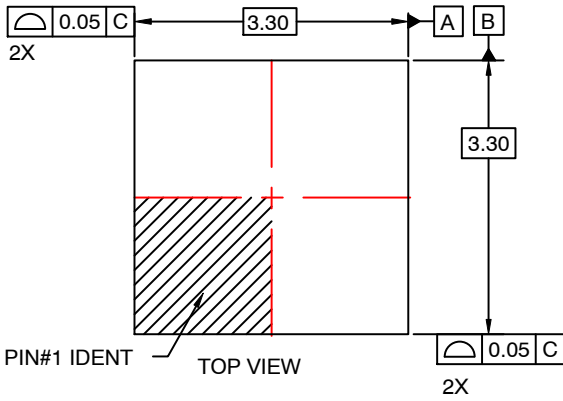
Device	Device Marking	Package	Reel Size	Tape Width	Shipping [†]
NTTFS115P10M5	115P10M5	WDFN8 (Pb-Free)	13"	12 mm	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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PACKAGE DIMENSIONS

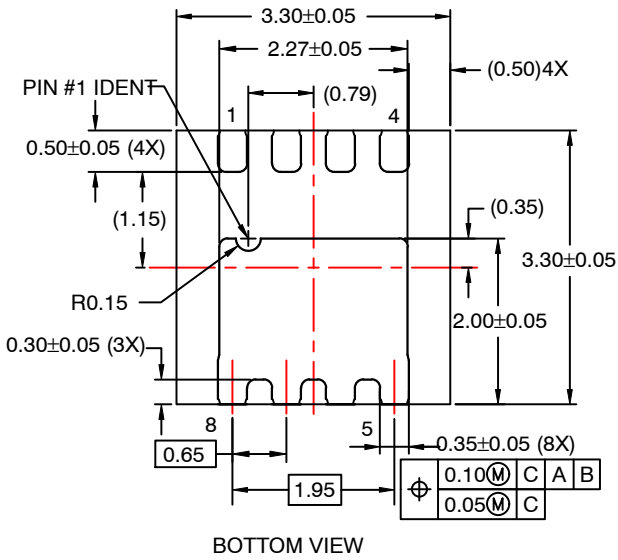
WDFN8 3.3x3.3, 0.65P
CASE 511DH
ISSUE O




RECOMMENDED LAND PATTERN

NOTES:

- A. DOES NOT CONFORM TO JEDEC REGISTRATION MO-229
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.



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